

**Silicon NPN Darlington Power Transistors**

**2SC3146**

**DESCRIPTION**

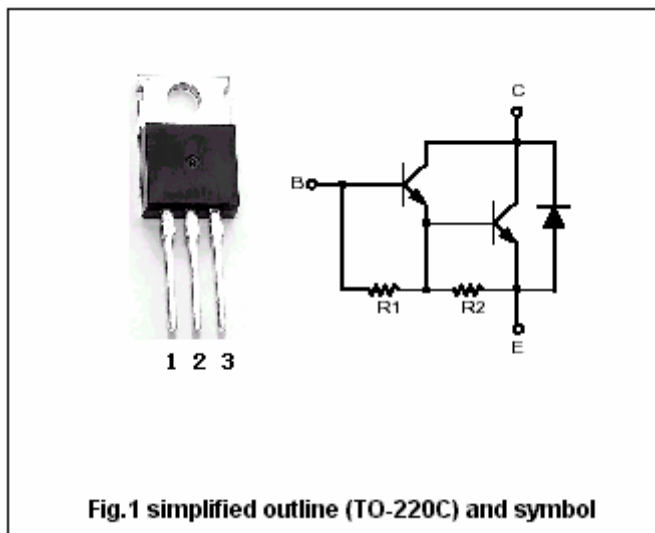
- With TO-220C package
- High switching speed
- High DC current gain
- Wide area of safe operation
- Complement to type 2SA1260

**APPLICATIONS**

- 60V/7A for High-Speed Drivers Applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**ABSOLUTE MAXIMUM RATINGS (T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	70	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current-DC		7	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	40	W
		T <sub>a</sub> =25°C	1.75	
T <sub>j</sub>	Junction temperature		125	°C
T <sub>stg</sub>	Storage temperature		-55~125	°C

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =50mA ; R <sub>BE</sub> =∞	60			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =5mA ; I <sub>E</sub> =0	70			V
V <sub>CE(sat)-1</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3.5A , I <sub>B</sub> =7mA			1.5	V
V <sub>CE(sat)-2</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3.5A , I <sub>B</sub> =7mA			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =40V, I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			3.0	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =3.5A ; V <sub>CE</sub> =2V	2000			

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PACKAGE OUTLINE

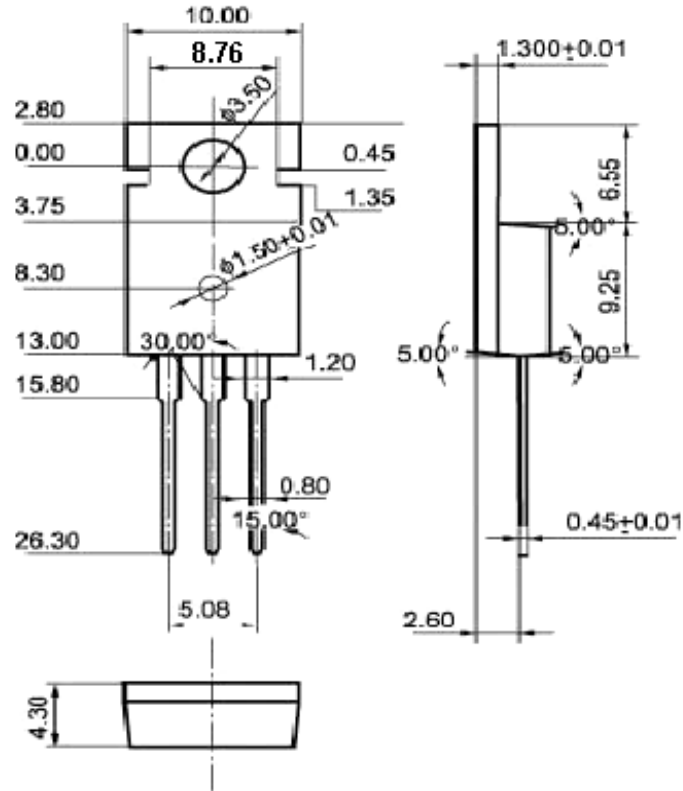


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)